# **Fixed Current-Limiting Power-Distribution Switches**

The NCP382 is a single input dual outputs high side power-distribution switch designed for applications where heavy capacitive loads and short-circuits are likely to be encountered. The device includes an integrated 80 mQ, P-channel MOSFET. The device limits the output current to a desired level by switching into a constant-current mode when the output load exceeds the current-limit threshold or a short is present. The current-limit threshold is internally fixed. The power-switches rise and fall times are controlled to minimize current ringing during switching.

The FLAG logic output asserts low during overcurrent or overtemperature conditions. The switch is controlled by a logic enable input active high or low.

#### Features

- 2.5 V 5.5 V Operating Range
- 80 mΩ High–Side MOSFET
- Current Limit: Fixed 500 mA, 1 A, 1.5 A and 2 A
- Undervoltage Lock–Out (UVLO)
- Soft-Start Prevents Inrush Current
- Thermal Protection
- Soft Turn–Off
- Enable Active High or Low (EN or  $\overline{EN}$ )
- Compliance to IEC61000–4–2 (Level 4)
  - ◆ 8.0 kV (Contact)
  - 15 kV (Air)
- UL Listed for SOIC package (NCP382xDxxxx) File No. E343275
- IEC60950 Edition 2 for SOIC package (NCP382xDxxxx) -Amendments 1 & 2 Certified (CB Scheme)
- These are Pb–Free Devices

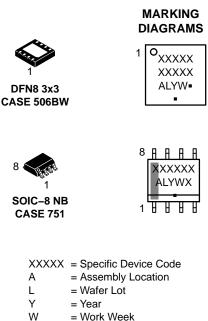
#### **Typical Applications**

- Laptops
- USB Ports/Hubs
- TVs



# **ON Semiconductor®**

www.onsemi.com



= Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

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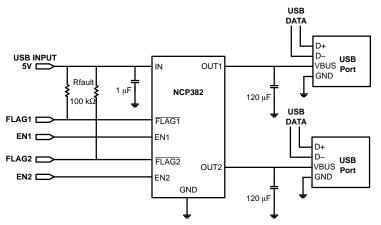
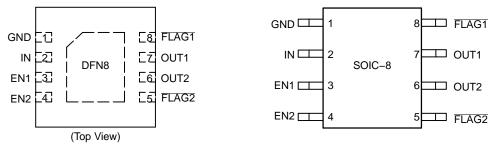


Figure 1. Typical Application Circuit





## **PIN FUNCTION DESCRIPTION**

Pin Name	Туре	Description
EN1	I	Enable 1 input, logic low/high (i.e. EN or EN) turns on power switch.
EN2	I	Enable 2 input, logic low/high (i.e. EN or EN) turns on power switch.
GND	Р	Ground connection.
IN	Р	Power–switch input voltage; connect a 1 $\mu F$ or greater ceramic capacitor from IN to GND as close as possible to the IC.
FLAG1	0	Active–low open–drain output 1, asserted during overcurrent or overtemperature conditions. Connect a 10 k $\Omega$ or greater resistor pull–up, otherwise leave unconnected.
FLAG2	0	Active–low open–drain output 2, asserted during overcurrent or overtemperature conditions. Connect a 10 k $\Omega$ or greater resistor pull–up, otherwise leave unconnected.
OUT1	0	Power–switch output1; connect a 1 $\mu$ F ceramic capacitor from OUT1 to GND, as close as possible to the IC. This minimum value is recommended for USB requirement in terms of load transient response and strong short circuits.
OUT2	0	Power–switch output2; connect a 1 $\mu$ F ceramic capacitor from OUT2 to GND, as close as possible to the IC. This minimum value is recommended for USB requirement in terms of load transient response and strong short circuits.

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
From IN to OUT1, From IN to OUT2 Supply Voltage (Note 1)	V <sub>IN</sub> , V <sub>OUT1</sub> , V <sub>OUT2</sub>	-7.0 to +7.0	V
IN, OUT1,OUT2, EN1, EN2, FLAG1, FLAG2 (Note 1)	V <sub>IN,</sub> V <sub>OUT1</sub> , V <sub>OUT2</sub> , V <sub>EN1</sub> , V <sub>EN2</sub> , V <sub>FLAG1</sub> , V <sub>FLAG2</sub>	-0.3 to +7.0	V
FLAG1, FLAG2 sink current	ISINK	1.0	mA
ESD Withstand Voltage (IEC 61000–4–2) (output only, when bypassed with 1.0 $\mu F$ capacitor minimum)	ESD IEC	15 Air, 8 contact	kV
Human Body Model (HBM) ESD Rating are (Note 2)	ESD HBM	2000	V
Machine Model (MM) ESD Rating are (Note 2)	ESD MM	200	V
Latch-up protection (Note 3) – Pins IN, OUT1, OUT2, FLAG1, FLAG2 – EN1, EN2	LU	100	mA
Maximum Junction Temperature (Note 4)	ТJ	-40 to + TSD	°C
Storage Temperature Range	T <sub>STG</sub>	-40 to + 150	°C
Moisture Sensitivity (Note 5)	MSL	Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. According to JEDEC standard JESD22-A108.

 This device series contains ESD protection and passes the following tests: Human Body Model (HBM) +/-2.0 kV per JEDEC standard: JESD22-A114 for all pins. Machine Model (MM) +/-200 V per JEDEC standard: JESD22-A115 for all pins.

3. Latch up Current Maximum Rating: ±100 mA per JEDEC standard: JESD78 class II.

4. A thermal shutdown protection avoids irreversible damage on the device due to power dissipation.

5. Moisture Sensitivity Level (MSL): 1 per IPC/JEDEC standard: J-STD-020.

## **OPERATING CONDITIONS**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>IN</sub>	Operational Power Supply			2.5		5.5	V
V <sub>ENX</sub>	Enable Voltage			0		5.5	
T <sub>A</sub>	Ambient Temperature Range			-40	25	+85	°C
I <sub>SINK</sub>	FLAG sink current					1	mA
C <sub>IN</sub>	Decoupling input capacitor			1			μF
C <sub>OUTX</sub>	Decoupling output capacitor		USB port per Hub	120			μF
$R_{\thetaJA}$	Thermal Resistance Junction-to-Air	DFN-8 package (Notes 6 and 7)			140		°C/W
		SOIC-8 package (Notes 6 and 7)			210		°C/W
ΤJ	Junction Temperature Range			-40	25	+125	°C
I <sub>OUTX</sub>			DFN-8 package			2	А
	current	SOIC-8 package				1.5	А
PD	Power Dissipation Rating (Note 8)	$T_A \le 25^{\circ}C$ DFN-8 package		850			mW
			SOIC-8 package	570			mW
		T <sub>A</sub> = 85°C	DFN-8 package	428			mW
			SOIC-8 package	285			mW

6. A thermal shutdown protection avoids irreversible damage on the device due to power dissipation.

The R<sub>0JA</sub> is dependent of the PCB heat dissipation. Announced thermal resistance is the unless PCB dissipation and can be improve with 7. final PCB layout.

8. The maximum power dissipation  $(P_D)$  is given by the following formula:

$$\mathsf{P}_{\mathsf{D}} = \frac{\mathsf{T}_{\mathsf{JMAX}} - \mathsf{T}_{\mathsf{A}}}{\mathsf{R}_{\mathsf{\theta}\mathsf{JA}}}$$

ELECTRICAL CHARACTERISTICS Min & Max Limits apply for T<sub>A</sub> between -40°C to +85°C and T<sub>J</sub> up to + 125°C for V<sub>IN</sub> between 2.5 V to 5.5 V (Unless otherwise noted). Typical values are referenced to  $T_A = +25^{\circ}C$  and  $V_{IN} = 5$  V.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
POWER S	SWITCH	-			-		
R <sub>DS(on)</sub>	Static drain-source on-state resistance	$T_{J} = 25^{\circ}C, V_{IN} = 3.6 V \text{ to } 5 V$			80	110	mΩ
	(SOIC–8 Package)	V <sub>IN</sub> = 5 V	V <sub>IN</sub> = 5 V -40°C < T <sub>J</sub> < 125°C			140	
R <sub>DS(on)</sub>	Static drain-source on-state resistance	$T_{\rm J} = 25^{\circ}$	$^{\circ}$ C, V <sub>IN</sub> = 3.6 V to 5 V		80	95	mΩ
	(DFN8 Package)	$V_{IN} = 5 V$	–40°C < T <sub>J</sub> < 125°C			100	
Τ <sub>R</sub>	Output rise time	$V_{IN} = 5 V$	$C_{LOAD} = 1 \mu F,$	0.3	1.0	1.5	ms
		V <sub>IN</sub> = 2.5 V	$R_{LOAD} = 100 \Omega$ (Note 9)	0.2	0.65	1.0	
Τ <sub>F</sub>	Output fall time	V <sub>IN</sub> = 5 V		0.1		0.5	
		V <sub>IN</sub> = 2.5 V		0.1		0.5	
		1		10	<u> </u>		V
V <sub>IH</sub>	High-level input voltage	-		1.2		0.4	V
VIL	Low-level input voltage			0.5		0.4	V
I <sub>ENx</sub>			$x = 0 \text{ V}, \text{ V}_{\overline{\text{ENx}}} = 5 \text{ V}$	-0.5		0.5	μΑ
T <sub>ON</sub>	Turn on time	C <sub>LOAD</sub> = 1 μl	F, $R_{LOAD} = 100 \Omega$ (Note 9)	1.0		3.0	ms
	Turn off time			1.0		3.0	ms
CURREN				0.5	0.0	0.7	•
I <sub>OCP</sub>	Current–limit threshold (Maximum DC output current I <sub>OUTX</sub> delivered to load)		= 5 V, Fixed 0.5 A = 5 V, Fixed 1.0 A	0.5	0.6	0.7	A
			= 5 V, Fixed 1.5 A	1.0	1.2 1.75	1.4 2.0	
			= 5 V, Fixed 2 A	1.5	2.25	2.0	-
T <sub>DET</sub>	Response time to short circuit	V IN	$V_{IN} = 5 V$	2	2.20	2.5	μs
	Regulation time		VIN - 5 V	2.0	3.0	4.0	μs ms
T <sub>REG</sub> T <sub>OCP</sub>	Over current protection time			14	20	26	ms
	OVER CUTERIN PROJECTION TIME			14	20	20	1115
V <sub>UVLO</sub>	IN pin low-level input voltage		V <sub>IN</sub> rising	2.0	2.35	2.5	V
	IN pin hysteresis		$T_J = 25^{\circ}C$	2.0	40	60	mV
V <sub>HYST</sub>	Re–arming Time	$V_{\rm IN}$ rising		5.0	10	15	
			VINITSHIG	5.0	10	10	ms
	Low-level output supply current	V 5 V. No.	load on OUTX, Device OFF	1	2.0	3.0	μA
IINOFF		$V_{IN} = 5 V, 100$ $V_{ENX}$	= 0 V or $V_{ENX}$ = 5 V		2.0	5.0	μΛ
I <sub>INON</sub>	High-level output supply current	0.5 A	$T_J = 25^{\circ}C$			95	μΑ
			$T_J = 85^{\circ}C$			100	
		1 and 1.5 A	T <sub>J</sub> = 25°C T <sub>J</sub> = 85°C			115 125	
		2 A	T <sub>J</sub> = 25°C T <sub>J</sub> = 85°C			130 140	
I <sub>REV</sub>	Reverse leakage current	V <sub>OUTX</sub> = 5 V, V <sub>IN</sub> = 0 V	$T_J = 25^{\circ}C$		1.0	2.0	μΑ
FLAG PIN	1		ļ	1			
V <sub>OL</sub>	FLAGX output low voltage		FLAGX = 1 mA			400	mV
ILEAK	Off-state leakage	$V_{FLAGX} = 5 V$			0.02	1	μA
T <sub>FLG</sub>	FLAGX deglitch	FLAGX de–assertion time due to overcurrent		4	6	9	ms
T <sub>FOCP</sub>	FLAGX deglitch	FLAGX assertion due to overcurrent		6	8	12	ms
	L SHUTDOWN			1			
T <sub>SD</sub>	Thermal shutdown threshold				140		°C
T <sub>SDOCP</sub>	Thermal regulation threshold				125		°C
T <sub>RSD</sub>	Thermal regulation rearming threshold				115		°C
	eters are guaranteed for Cusus and Pusus a			1	110	I	, U

Parameters are guaranteed for C<sub>LOAD</sub> and R<sub>LOAD</sub> connected to the OUTX pin with respect to the ground.
DFN package only.
Guaranteed by characterization.

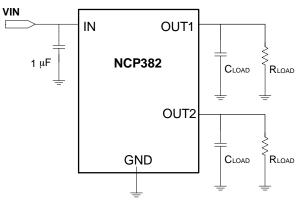
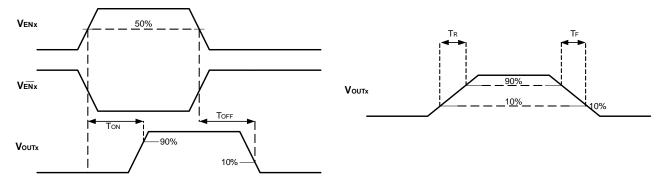


Figure 3. Test Configuration





## **BLOCK DIAGRAM**

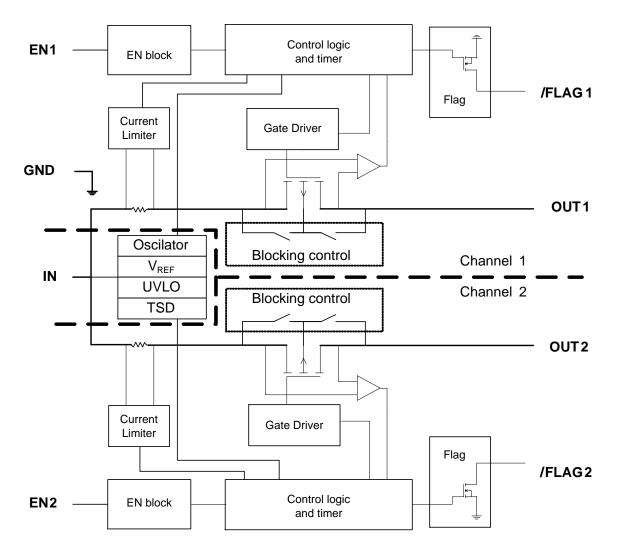


Figure 5. Block Diagram

#### FUNCTIONAL DESCRIPTION

#### Overview

The NCP382 is a dual high side power distribution switches designed to protect the input supply voltage in case of heavy capacitive loads, short circuit or over current. In addition, the high side MOSFETs are turned off during undervoltage or thermal shutdown condition. Thanks to the soft start circuitry, NCP382 is able to limit large current and voltage surges.

#### **Overcurrent Protection**

NCP382 switches into a constant current regulation mode when the output current is above the  $I_{OCP}$  threshold. Depending on the load, the output voltage is decreased accordingly.

 In case of hot plug with heavy capacitive load, the output voltage is brought down to the capacitor voltage. The NCP382 will limit the current to the I<sub>OCP</sub> threshold value until the charge of the capacitor is completed.

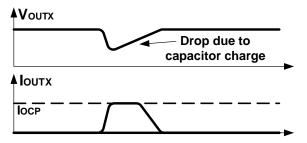


Figure 6. Heavy Capacitive Load

In case of overload, the current is limited to the I<sub>OCP</sub> value and the voltage value is reduced according to the load by the following relation:

$$V_{OUTX} = R_{LOAD2} \times I_{OCP}$$
 (eq. 1)

Voutx

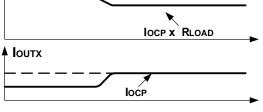
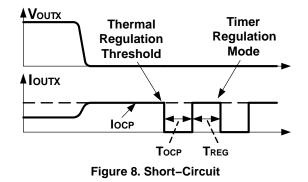


Figure 7. Overload

- In case of short circuit or huge load, the current is limited to the  $I_{OCP}$  value within  $T_{DET}$  time until the short condition is removed. If the output remains shorted or tied to a very low voltage, the junction temperature of the chip exceeds  $T_{SDOCP}$  value and the device enters in thermal shutdown (MOSFET is turned–off).



Then, the device enters in timer regulation mode, described in 2 phases:

- Off-phase: Power MOSFET is off during T<sub>OCP</sub> to allow the die temperature to drop.
- On-phase: regulation current mode during T<sub>REG</sub>. The current is regulated to the I<sub>OCP</sub> level.

The timer regulation mode allows the device to handle high thermal dissipation (in case of short circuit for example) within temperature operating condition.

NCP382 stays in on-phase/off-phase loop until the over current condition is removed or enable pin is toggled.

**Remark:** other regulation modes can be available for different applications. Please contact our On Semiconductor representative for availability.

## **FLAG** Indicator

The FLAG pin is an open-drain MOSFET asserted low during overcurrent or overtemperature conditions. When an overcurrent fault is detected on the power path, FLAG pin is asserted low at the end of the associate deglitch time (TFOCP). Thanks to this feature, the FLAG pin is not tied low during the charge of a heavy capacitive load or a voltage transient on output. The FLAG pin remains low until the fault is removed. Then, the FLAG pin goes high at the end of T<sub>FGL</sub>

#### Undervoltage Lock-out

Thanks to a built–in under voltage lockout (UVLO) circuitry, the output remains disconnected from input until  $V_{IN}$  voltage is above  $V_{UVLO}$ . This circuit has a  $V_{HYST}$  hysteresis witch provides noise immunity to transient condition.

#### Thermal Sense

Thermal shutdown turns off the power MOSFET if the die temperature exceeds  $T_{SD}$ . A built-in hysteresis prevents the part from turning on until the die temperature cools at TRSD.

supply.

#### **Enable Input**

Enable pin must be driven by a logic signal (CMOS or TTL compatible) or connected to the GND or VIN. A logic low on  $\overline{\text{ENX}}$  or high on ENX turns–on the device. A logic high on  $\overline{\text{ENX}}$  or low on ENX turns off device and reduces the current consumption down to I<sub>INOFF</sub>.

#### **Blocking Control**

The blocking control circuitry switches the bulk of the power MOS. When the part is off, the body diode limits the

#### **APPLICATION INFORMATION**

#### **Power Dissipation**

The junction temperature of the device depends on different contributing factors such as board layout, ambient temperature, device environment, etc... Yet, the main contributor in term of junction temperature is the power dissipation of the power MOSFET. Assuming this, the power dissipation and the junction temperature in normal mode can be calculated with the following equations:

$$\mathsf{P}_{\mathsf{D}} = \mathsf{R}_{\mathsf{DS}(\mathsf{on})} \times \left( \left( \mathsf{I}_{\mathsf{OUT1}} \right)^2 + \left( \mathsf{I}_{\mathsf{OUT2}} \right)^2 \right) \quad (\mathsf{eq. 2})$$

P <sub>D</sub>	= Power dissipation (W)					
R <sub>DS(on)</sub>	= Power MOSFET on resist	ance $(\Omega)$				
I <sub>OUTx</sub>	= Output current in channel X (A)					
	$T_J = P_D \times R_{\theta JA} + T_A$	(eq. 3)				

TJ	= Junction temperature (°C)
$R_{\theta JA}$	= Package thermal resistance (°C/W)
T <sub>A</sub>	= Ambient temperature (°C)

Power dissipation in regulation mode can be calculated by taking into account the drop  $V_{IN} - V_{OUTX}$  link to the load by the following relation:

leakage current IREV from OUTX to IN. In this mode, anode

of the body diode is connected to IN pin and cathode is

connected to OUTX pin. In operating condition, anode of

the body diode is connected to OUTX pin and cathode is

connected to IN pin preventing the discharge of the power

$$\begin{split} \mathsf{P}_\mathsf{D} &= \left( \left( \mathsf{V}_\mathsf{IN} - \mathsf{R}_\mathsf{LOAD1} \times \mathsf{I}_\mathsf{OCP} \right) + \left( \mathsf{V}_\mathsf{IN} - \mathsf{R}_\mathsf{LOAD2} \times \mathsf{I}_\mathsf{OCP} \right) \right) \\ & \times \mathsf{I}_\mathsf{OCP} \end{split} \tag{eq. 4}$$

PD	= Power dissipation (W)
V <sub>IN</sub>	= Input Voltage (V)
R <sub>LOADX</sub>	= Load Resistance on channel X ( $\Omega$ )
I <sub>OCP</sub>	= Output regulated current (A)

#### **PCB** Recommendations

The NCP382 integrates two PMOS FET rated up to 2 A, and the PCB design rules must be respected to properly evacuate the heat out of the silicon. The DFN8 PAD1 must be connected to ground plane to increase the heat transfer if necessary. Of course, in any case, this pad must not connect to any other potential. By increasing PCB area, the  $R_{0JA}$  of the package can be decreased, allowing higher current.

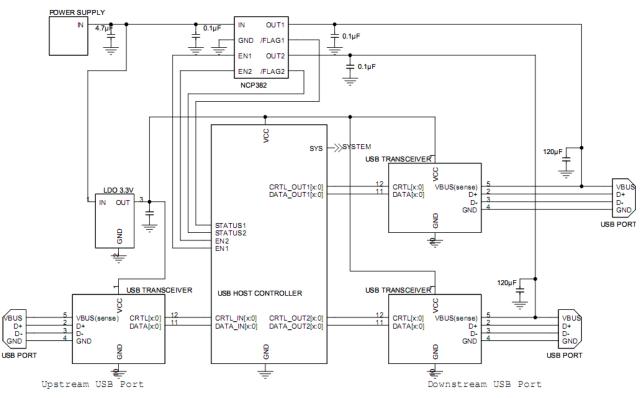


Figure 9. USB Host Typical Application

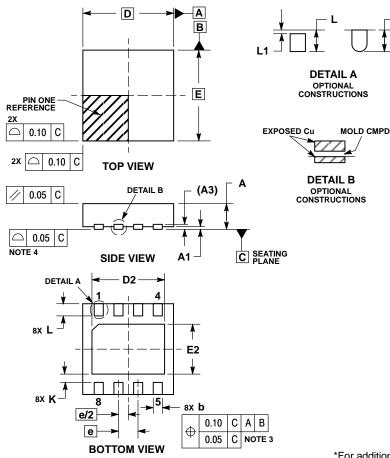
#### **ORDERING INFORMATION**

Device	Marking	Active Enable Level	Over Current Limit	Evaluation Board	UL 236 7	IEC60950 Ed2 (CB Scheme)	IEC60950 Ed2 Ad1, Ad2	Package	Shipping <sup>†</sup>
NCP382LMN05- AATXG	382 L05		0.5 A	NCP382LM N05AGEVB	Ν	Ν	N		
NCP382LMN10- AATXG	382 L10	ENx	1.0 A	NCP382LM N10AGEVB	N	N	N		
NCP382LMN15- AATXG	382 L15	Low	1.5 A	NCP382LM N15AGEVB	Ν	Ν	N		
NCP382LMN20- AATXG	382 L20	1	2.0 A	NCP382LM N20AGEVB	N	N	N	DFN8	3000 /
NCP382HMN05- AATXG	382 H05		0.5 A	NCP382HM N05AGEVB	N	N	N	(Pb-Free)	Tape / Reel
NCP382HMN10- AATXG	382 H10	ENx	1.0 A	NCP382HM N10AGEVB	N	N	N		
NCP382HMN15- AATXG	382 H15	High	1.5 A	NCP382HM N15AGEVB	Ν	N	N		
NCP382HMN20- AATXG	382 H20		2.0 A	NCP382HM N20AGEVB	N	N	N		
NCP382LD05AA- R2G	382L05		0.5 A	NCP382LD 05AAGEVB	Y	Y	Y		
NCP382LD10AA- R2G	382L10	ENx Low	1.0 A	NCP382LD 10AAGEVB	Y	Y	Y		
NCP382LD15AA- R2G	382L15		1.5 A	NCP382LD 15AAGEVB	Y	Y	Y	SOIC–8 (Pb–Free)	2500 /
NCP382HD05A- AR2G	382H05		0.5 A	NCP382HD 05AAGEVB	Y	Y	Y		Tape / Reel
NCP382HD10A- AR2G	382H10	ENx High	1.0 A	NCP382HD 10AAGEVB	Y	Y	Y		
NCP382HD15A- AR2G	382H15		1.5 A	NCP382HD 15AAGEVB	Y	Y	Y	1	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

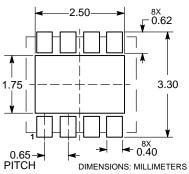
#### DFN8, 3x3, 0.65P CASE 506BW ISSUE O



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP. 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

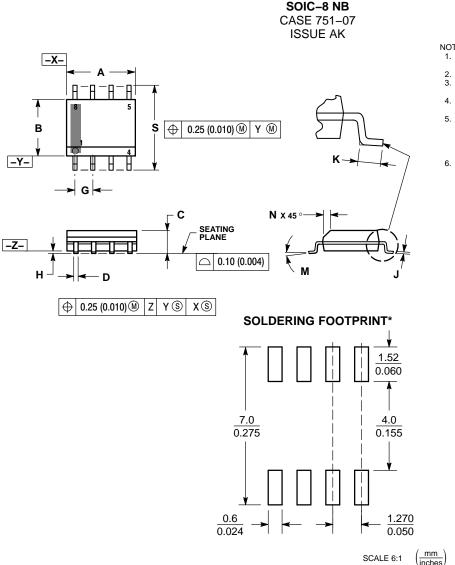
	MILLIMETERS				
DIM	MIN	MAX			
Α	0.80	1.00			
A1	0.00	0.05			
A3	0.20	REF			
b	0.25	0.35			
D	3.00	3.00 BSC			
D2	2.30	2.50			
Е	3.00	BSC			
E2	1.55	1.75			
е	0.65	BSC			
к	0.20				
L	0.35	0.45			
L1	0.00	0.15			

# RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751–01 THRU 751–06 ARE OBSOLETE. NEW STANDARD IS 751–07.

	MILLIN	IETERS	INC	CHES					
DIM	MIN	MAX	MIN	MAX					
Α	4.80	5.00	0.189	0.197					
В	3.80	4.00	0.150	0.157					
С	1.35	1.75	0.053	0.069					
D	0.33 0.51		0.013	0.020					
G	1.27	7 BSC	0.050 BSC						
Н	0.10	0.25	0.004	0.010					
L	0.19	0.25	0.007	0.010					
κ	0.40 1.27		0.016	0.050					
Μ	0 °	8 °	0 °	8 °					
Ν	0.25	0.50	0.010	0.020					
S	5.80	6.20	0.228	0.244					

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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